Preferred Device

NPN Silicon Expitaxial Transistor

This family of NPN Silicon Epitaxial transistors is designed for use as a general purpose amplifier and in switching applications. The device is housed in the SOT-223 package which is designed for medium power surface mount applications.

Features

- High Voltage: V_{(BR)CEO} of 250 and 350 V
- The SOT-223 Package can be Soldered Using Wave or Reflow
- SOT-223 Package Ensures Level Mounting, Resulting in Improved Thermal Conduction, and Allows Visual Inspection of Soldered Joints
- The Formed Leads Absorb Thermal Stress During Soldering, Eliminating the Possibility of Damage to the Die
- PNP Complement is BSP16T1
- Moisture Sensitivity Level (MSL): 1
- ESD: Human Body Model (HBM) = 4 KV Machine Model (MM) = 400 V
- Pb-Free Package is Available

MAXIMUM RATINGS (T_C = 25° C unless otherwise noted)

| Rating | Symbol | Value | Unit |
|---------------------------------------|------------------|-------|------|
| Collector-Emitter Voltage (Open Base) | V _{CEO} | 350 | Vdc |
| Collector-Base Voltage (Open Emitter) | V _{CBO} | 400 | Vdc |
| Emitter-Base Voltage (Open Collector) | V _{EBO} | 5.0 | Vdc |
| Collector Current (DC) | Ι _C | 100 | mAdc |

THERMAL CHARACTERISTICS

| Characteristic | Symbol | Max | Unit |
|--|------------------|--------------|------------|
| Total Power Dissipation @ T _A = 25°C (Note 1) Derate above 25°C | P _D | 0.8 6.4 | W mW/°C |
| Thermal Resistance, Junction- to- Ambient | R_{\thetaJA} | 156 | °C/W |
| Junction and Storage Temperature Range | T _{stg} | - 65 to +150 | °C |

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

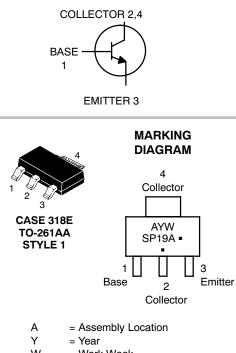
1. Device mounted on a FR-4 glass epoxy printed circuit board using minimum recommended footprint.

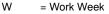


ON Semiconductor®

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SOT- 223 PACKAGE NPN SILICON HIGH VOLTAGE TRANSISTOR SURFACE MOUNT





SP19A = Specific Device Code

= Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

| Device | Package | Shipping [†] |
|-----------|----------------------|-----------------------|
| BSP19AT1 | SOT-223 | 1000 / Tape & Reel |
| BSP19AT1G | SOT-223 (Pb-Free) | 1000 / Tape & Reel |

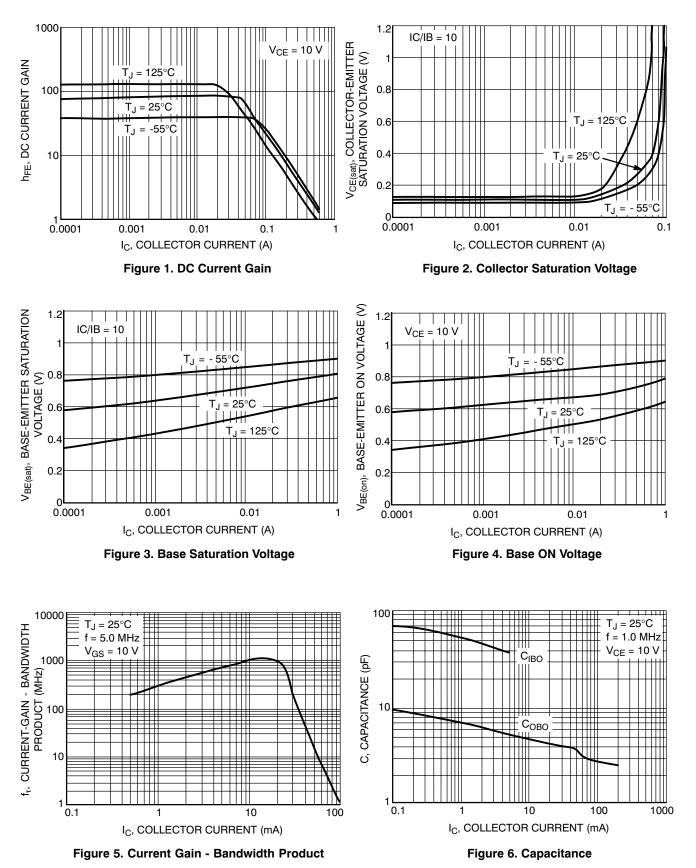
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Preferred devices are recommended choices for future use and best overall value.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

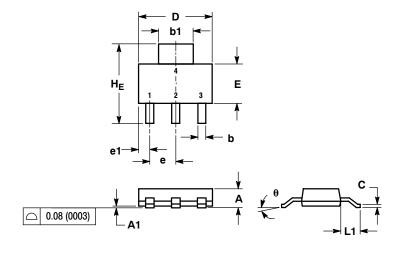
| Characteristics | Symbol | Min | Max | Unit |
|---|----------------------|-----|-----|------|
| OFF CHARACTERISTICS | | | | |
| Collector-Emitter Breakdown Voltage ($I_C = 1.0 \text{ mAdc}, I_B = 0$) | V _{(BR)CEO} | 350 | - | Vdc |
| Collector-Base Cutoff Current (V_{CB} = 400 Vdc, I _E = 0) | Ісво | - | 20 | nAdc |
| Emitter-Base Cutoff Current ($V_{EB} = 5.0 \text{ Vdc}, I_C = 0$) | I _{EBO} | - | 10 | μAdc |
| ON CHARACTERISTICS (Note 2) | | | | |
| DC Current Gain (I _C = 20 mAdc, V _{CE} = 10 Vdc) | h _{FE} | 40 | - | - |
| Current-Gain — Bandwidth Product ($I_C = 10 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}, f = 5.0 \text{ MHz}$) | fT | 70 | - | MHz |
| Collector-Emitter Saturation Voltage ($I_C = 50 \text{ mAdc}, I_B = 4.0 \text{ mAdc}$) | V _{CE(sat)} | - | 0.5 | Vdc |
| Base-Emitter Saturation Voltage $(I_C = 50 \text{ mAdc}, I_B = 4.0 \text{ mAdc})$ | V _{BE(sat)} | - | 1.3 | Vdc |

2. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle = 2.0%



PACKAGE DIMENSIONS

SOT-223 (TO-261) CASE 318E-04 ISSUE L



NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

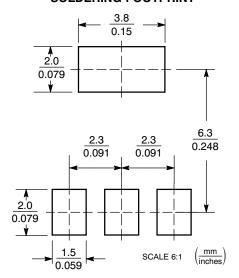
2. CONTROLLING DIMENSION: INCH.

STYLE 1:

PIN 1. BASE 2. COLLECTOR 3. EMITTER 4. COLLECTOR

| | MILLIMETERS | | | INCHES | | |
|-----|-------------|------|------|--------|-------|-------|
| DIM | MIN | NOM | MAX | MIN | NOM | MAX |
| Α | 1.50 | 1.63 | 1.75 | 0.060 | 0.064 | 0.068 |
| A1 | 0.02 | 0.06 | 0.10 | 0.001 | 0.002 | 0.004 |
| b | 0.60 | 0.75 | 0.89 | 0.024 | 0.030 | 0.035 |
| b1 | 2.90 | 3.06 | 3.20 | 0.115 | 0.121 | 0.126 |
| С | 0.24 | 0.29 | 0.35 | 0.009 | 0.012 | 0.014 |
| D | 6.30 | 6.50 | 6.70 | 0.249 | 0.256 | 0.263 |
| E | 3.30 | 3.50 | 3.70 | 0.130 | 0.138 | 0.145 |
| е | 2.20 | 2.30 | 2.40 | 0.087 | 0.091 | 0.094 |
| e1 | 0.85 | 0.94 | 1.05 | 0.033 | 0.037 | 0.041 |
| L1 | 1.50 | 1.75 | 2.00 | 0.060 | 0.069 | 0.078 |
| HE | 6.70 | 7.00 | 7.30 | 0.264 | 0.276 | 0.287 |
| θ | 0° | - | 10° | 0° | - | 10° |

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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